LASER ANNEALING METHOD AND APPARATUS

ABSTRACT

Disclosed are a laser annealing method and apparatus capable of forming a crystalline semiconductor thin film on the entire surface of a substrate without sacrificing the uniformity of crystallinity in a seam portion in a long-axis direction of laser light, the crystalline semiconductor thin film having good properties and high uniformity to an extent that the seam portion is not visually recognizable.

During the irradiation of a linear beam, portions corresponding to the edges of the linear beam are shielded by a mask 10 which is disposed on the optical path of a laser light 2, and the mask 10 is operated so that the amount of shielding is periodically increased and decreased.

Fig. 3A